



PNP General Purpose Amplifier

Features

We declare that the material of product compliance

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Maximum Ratings (Ta=25 Unless otherwise specified)

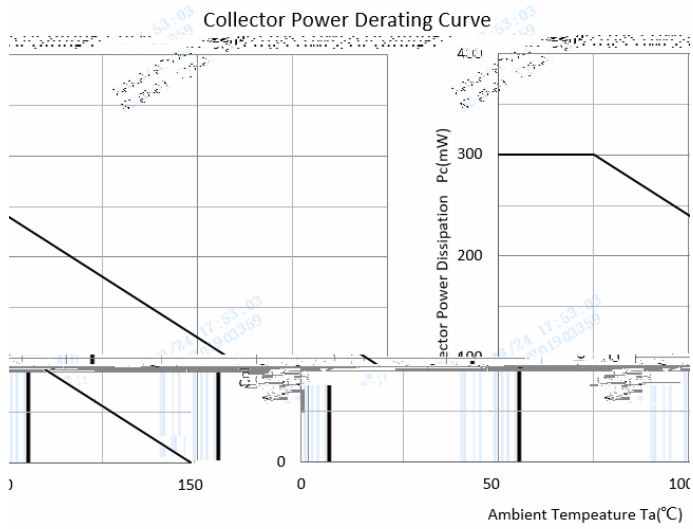
Item	Symbol	Unit	Conditions	Value
Collector-Base Voltage	V_{CBO}	V	$I_C=-100\mu A, I_E=0$	-80
Collector-Emitter Voltage	V_{CEO}	V	$I_C=-10mA, I_B=0$	-60
Emitter-Base Voltage	V_{EBO}	V	$I_E=-100\mu A, I_C=0$	-5
Collector Current	I_C	A		-1
Collector Power Dissipation	P_C	mW		300
Thermal Resistance From Junction to Ambient	R_{JA}	/W		417
Operation Junction Temperature	T_J			150
Storage Temperature	T_{STG}			-55 to +150

Electrical Characteristics Ta=25 Unless otherwise specified

Item	Symbol	Unit	Conditions	Min	Type	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	V	$I_C=-100\mu A, I_E=0$	-80		
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	V	$I_C=-10mA, I_B=0$	-60		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	V	$I_E=-100\mu A, I_C=0$	-5		
Collector-Base cut-off current	I_{CBO}	μA	$V_{CB}=-60V, I_E=0$			-0.1
Emitter-Base cut-off current	I_{EBO}	μA	$V_{EB}=-4V, I_C=0$			-0.1
DC current gain	h_{FE1}		$V_{CE}=-5V, I_C=-1mA$	100		
	h_{FE2}		$V_{CE}=-5V, I_C=-500mA$	100		300
	h_{FE3}		$V_{CE}=-5V, I_C=-1A$	80		
	h_{FE4}		$V_{CE}=-5V, I_C=-2A$	15		
Collector-emitter saturation voltage	$V_{CE(sat)}$	V	$I_C=-500mA, I_B=-50mA$			-0.3
		V	$I_C=-1A, I_B=-100mA$			-0.6
Base-emitter saturation voltage	$V_{BE(sat)}$	V	$I_C=-1A, I_B=-100mA$			-1.2
Base-emitter voltage	V_{BE}	V	$V_{CE}=-5V, I_C=-1A$			-1
Transition frequency	f_T	MHz	$V_{CE}=-10V, I_C=-50mA, f=100MHz$	150		
Collector-Base Output Capacitance	C_{ob}	pF	$V_{CB}=-10V, I_E=0, f=1MHz$		10	

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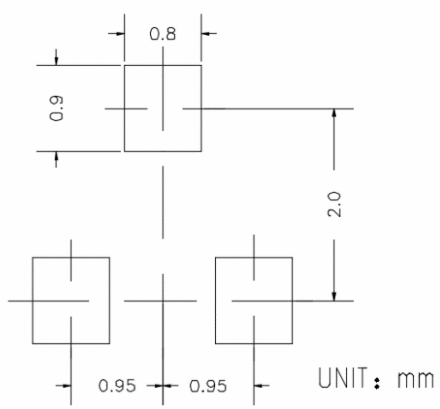


Ordering Information (Example)

PREFERED P/N



SOT-23 Soldering Footprint



SUGGESTED SOLDER PAD LAYOUT

